

Magneto-transport properties governed by the antiferromagnetic fluctuations in heavy fermion superconductor CeIrIn₅

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In quasi-two dimensional Ce(Ir,Rh)In₅ system, it has been suggested that the phase diagram contains two distinct domes with different heavy fermion superconducting states. We here report the systematic pressure dependence of the electron transport properties in the normal state of CeRh_{0.2}Ir_{0.8}In₅ and CeIrIn₅, which locates in first and second superconducting dome, respectively. We observed non-Fermi liquid behavior at low temperatures in both compounds, including non-quadratic T -dependence of the resistivity, large enhancement of the Hall coefficient, and the violation of the Kohler's rule in the magnetoresistance. We show that the cotangent of Hall angle $\cot \Theta_H$ varies as T^2 , and the magnetoresistance is quite well scaled by the Hall angle as $\Delta\rho_{xx}/\rho_{xx} \propto \tan^2 \Theta_H$. The observed transport anomalies are common features of CeMIn₅ (M =Co, Rh, and Ir) and high- T_c cuprates, suggesting that the anomalous transport properties observed in CeIrIn₅ are mainly governed by the antiferromagnetic spin fluctuations, not by the Ce-valence fluctuations which has been proposed to be the possible origin for the second superconducting dome.

PACS numbers: 71.27.+a,74.25.Fy,74.25.Dw,74.70.Tx

I. INTRODUCTION

The recent discoveries of heavy fermion compounds CeMIn₅ (M =Rh, Co, and Ir) give a unique opportunity to elucidate the interplay between the magnetism and the superconductivity. The ground state of these compounds can be tuned by pressure and chemical doping. CeCoIn₅¹ and CeIrIn₅² are superconductors with the transition temperature $T_c = 2.3$ K and 0.4 K at ambient pressure, respectively. On the other hand, CeRhIn₅ is an antiferromagnet with $T_N = 3.8$ K at ambient pressure and shows superconductivity under pressure.³ In CeCoIn₅ and CeRhIn₅, the thermodynamic and transport properties in the normal state exhibit a striking deviation from conventional Fermi liquid behavior,^{4,5,6} which is commonly observed in the systems in the vicinity of the antiferromagnetic (AF) quantum critical point (QCP). Then it is widely believed that the superconductivity in CeRhIn₅ and CeCoIn₅ is closely related to the AF fluctuations.

Recently, it has been suggested that CeIrIn₅ should be distinguished from CeCoIn₅ and CeRhIn₅, although all three compounds share similar quasi-two dimensional (2D) band structure.^{7,8} Figure 1 depicts the schematic temperature - x (T - x) phase diagram of CeRh_{1-x}Ir_xIn₅ and temperature - pressure (T - P) phase diagram of CeIrIn₅.^{9,10} In this system the Rh substitution for Ir increases the c/a ratio, acting as a negative chemical pressure that increases AF correlations. In CeRh_{1-x}Ir_xIn₅, the ground state continuously evolves from AF metal ($x < 0.5$) to superconductivity ($x > 0.5$). T_c shows a maximum at $x \sim 0.7$ and exhibits a cusp-like minimum at $x \sim 0.9$, forming a first dome (SC1). The

superconductivity nature in SC1, which occurs in the proximity to AF QCP, should be essentially the same as CeCo(In_{1-x}Cd_x)₅¹² and CeRhIn₅.³ The strong AF fluctuations associated with the AF QCP nearby are observed in SC1.^{10,13} In CeIrIn₅ ($x = 1$), T_c increases with pressure and exhibits a maximum ($T_c = 1$ K) at $P \sim 3$ GPa, forming a second dome (SC2). The AF fluctuations in SC2 far from the AF QCP are strongly suppressed, compared with those in SC1.^{10,13,14} Moreover, it has been reported that the nature of the crossover behavior from non-Fermi to Fermi liquid in strong magnetic fields for CeIrIn₅ is very different from that for CeCoIn₅ and CeRhIn₅.^{15,16,17}

From the analogy to CeCu₂(Si_{1-x}Ge_x)₂ with two distinct superconducting domes,¹⁸ a possibility that the Ce-valence fluctuations play an important role for the normal and superconducting properties in CeIrIn₅ has been pointed out.¹⁹ For instance, it has been suggested that while the superconductivity in SC1 is magnetically mediated, the superconductivity in SC2 may be mediated by the Ce-valence fluctuations.²⁰ Thus the major outstanding question is whether the Ce-valence fluctuations play an important role for the physical properties of CeIrIn₅ in SC2 phase. Our previous studies indicate that the transport coefficients, including resistivity, Hall effect, and magnetoresistance, can be powerful tools to probe the AF spin fluctuations.^{21,22,23} In this paper, we report the systematic pressure study of the transport properties for CeRh_{0.2}Ir_{0.8}In₅ and CeIrIn₅, which locates in SC1 and SC2 phase, respectively. We provide several pieces of evidence that all the anomalous transport properties observed in CeIrIn₅ and CeRh_{0.2}Ir_{0.8}In₅ originate from the AF spin fluctuations irrespective of which supercon-

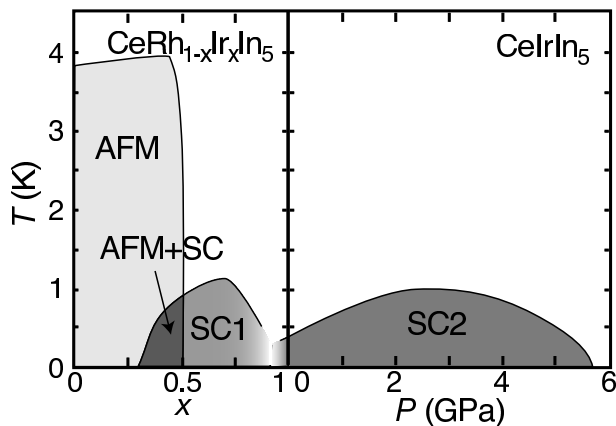


FIG. 1: Schematic T - x phase diagram for $\text{CeRh}_{1-x}\text{Ir}_x\text{In}_5$ and T - P phase diagram for CeIrIn_5 ^{9,10,11}.

ducting phase the system belongs to.

II. EXPERIMENTAL

The high quality single crystals of CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ were grown by the self-flux method. We performed all measurements on samples with a typical dimension of $\sim 1.0 \times 2.0 \times 0.1 \text{ mm}^3$ in the transverse geometry for $\mathbf{H} \parallel c$ and the current $\mathbf{J} \parallel a$. The Hall effect and transverse magnetoresistance were measured simultaneously. We obtained Hall resistivity from the transverse resistance by subtracting the positive and negative magnetic field data. Hydrostatic pressure up to 2.41 GPa were generated in a piston-cylinder type high pressure cell with oil as a transmitting fluid (Daphne 7373 : petroleum ether = 1 : 1). The pressure inside the cell was determined by the superconducting transition temperature of Pb.

III. RESULTS

A. Resistivity

Figures 2(a) and (b) show the temperature dependence of the resistivity ρ_{xx} in zero field at several pressures for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$, respectively. The overall feature of the temperature dependence for both compounds is typical in Ce-based heavy fermion compounds. On cooling from room temperature, ρ_{xx} first decreases and then increases due to dominant Kondo scattering. At lower temperatures, ρ_{xx} exhibits a metallic behavior after showing a broad maximum at around the temperature T_{coh} , shown by arrows. T_{coh} corresponds to the Fermi temperature of f electrons and the system becomes coherent below T_{coh} . T_{coh} increases with pressure. The insets of Figs. 2(a) and (b) show the low temperature data

of ρ_{xx} for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$, respectively. The resistivities of CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ are markedly different from the T^2 -behavior expected in Fermi liquid metals. At ambient pressure, ρ_{xx} varies as

$$\rho_{xx} \sim T^\alpha \quad (1)$$

with $\alpha \sim 1$ for CeIrIn_5 and ~ 0.7 for $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$. α increases with pressure for both systems and reaches ~ 1.4 at 2.4 GPa for CeIrIn_5 and ~ 1.3 at 2.19 GPa

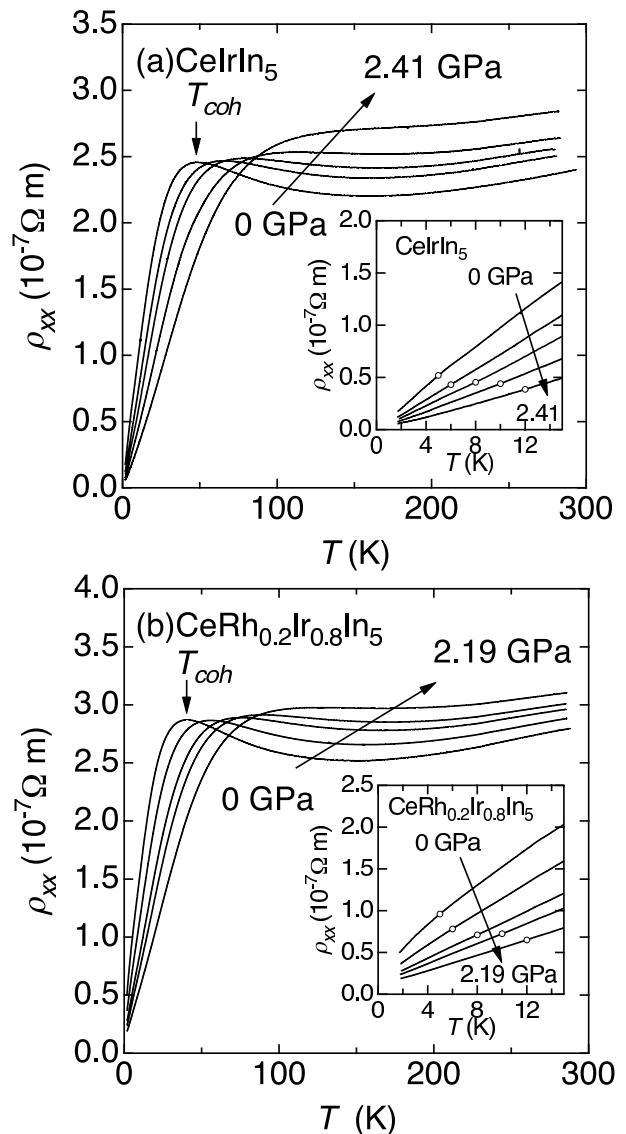


FIG. 2: (a) Temperature dependence of resistivity for CeIrIn_5 at 0, 0.56, 0.98, 1.59, and 2.41 GPa. (b) Temperature dependence of resistivity for $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ at 0, 0.49, 1.11, 1.50, and 2.19 GPa. Insets are expanded views at low temperatures. Downarrows drawn in main panels indicate T_{coh} at ambient pressure, where the resistivity shows a broad maximum, where the resistivity shows a minimum. Open circles shown in the insets indicate the resistivity at T_m where R_H shows a minimum. For detail, see the text in §.4.

for $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$, indicating that the Fermi liquid behavior is recovering by applying pressure. We note that these α -value is close to that reported in Ref. 24. These temperature and pressure dependence of resistivities for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ are very similar to those of CeCoIn_5 and CeRhIn_5 .^{22,23}

B. Hall effect

Figures 3 depict the Hall resistivity ρ_{xy} as a function of magnetic field at ambient pressure for CeIrIn_5 . The sign of ρ_{xy} is negative. At low temperatures, ρ_{xy} deviates from the H -linear dependence. Similar behavior is observed in $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$. Figures 4(a) and (b) show the temperature dependence of the Hall coefficient R_H in zero field limit defined as $R_H \equiv \lim_{H \rightarrow 0} \frac{d\rho_{xy}}{dH}$ at several pressures for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$, respectively. For comparison, R_H of LaIrIn_5 , which has no f -electron and has similar band structure to CeIrIn_5 , is plotted in the same figure. For LaIrIn_5 , R_H shows a shallow minimum at around 20 K and becomes nearly T -independent at low temperatures. The carrier number estimated from $R_H \sim 3 \times 10^{-10} \text{m}^3/\text{C}$ for LaIrIn_5 at low temperatures corresponds to nearly three electrons per unit cell, which is consistent with the number expected from the band structure, indicating $R_H \simeq 1/ne$ where n is the carrier number.

The Hall effect in CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ is distinctly different from that in LaIrIn_5 . The temperature dependence of R_H for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ is closely correlated with the resistivity. The down-arrow in Figs. 4 (a) and (b) indicates T_{coh} at ambient pressure determined by the resistivity peak in Figs. 2(a) and (b), respectively. In the high temperature regime above T_{coh} , R_H for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ shows weak T -dependence. Well above T_{coh} , R_H for both compounds well coincides with R_H of LaIrIn_5 , indicating $R_H \simeq 1/ne$. Below T_{coh} , R_H for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ decreases rapidly with decreasing T . At lower temperatures, R_H increases after showing minimum at T_m indi-

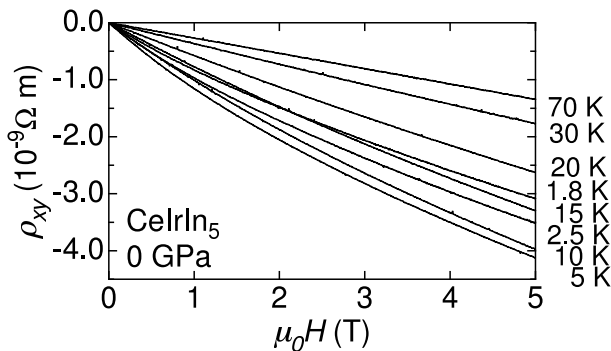


FIG. 3: Field dependence of ρ_{xy} for CeIrIn_5 at ambient pressure.

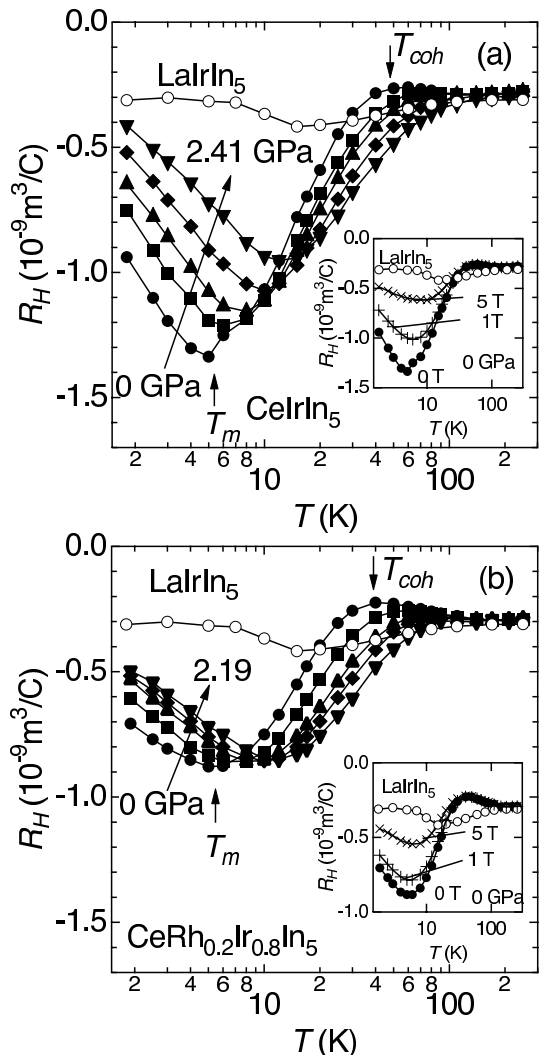


FIG. 4: (a) Temperature dependence of R_H for CeIrIn_5 at several pressures (0 (●), 0.56 (■), 0.98 (▲), 1.56 (◆), and 2.41 GPa (▼)) and for LaIrIn_5 at ambient pressure (○). R_H is defined by the zero-field limit for derivative of ρ_{xy} . Inset: Temperature dependence of R_H for CeIrIn_5 at 0 (●), 1 (+), and 5 T (×) at ambient pressure. (b) Temperature dependence of R_H for $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ at several pressures (0 (●), 0.49 (■), 1.11 (▲), 1.50 (◆) and 2.19 GPa (▼)) and for LaIrIn_5 at ambient pressure (○). Inset: Temperature dependence of R_H for $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ at 0 (●), 1 (+), and 5 T (×) at ambient pressure. Down and up arrows in main panels indicate T_{coh} at ambient pressure determined by the resistivity peak and T_m at ambient pressure, where R_H shows a minimum, respectively.

cated by up-arrows in Figs. 4(a) and (b). With increasing pressure, T_m increases and the enhancement of $|R_H|$ at low temperature regime is reduced for CeIrIn_5 .

The insets of Figs. 4 (a) and (b) show the temperature dependence of R_H at $\mu_0 H = 0, 1,$ and 5 T at ambient pressure for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$, respectively. R_H is defined by a field derivative of ρ_{xy} , $R_H \equiv d\rho_{xy}/dH$. The magnitude of R_H below T_{coh} is strongly suppressed by

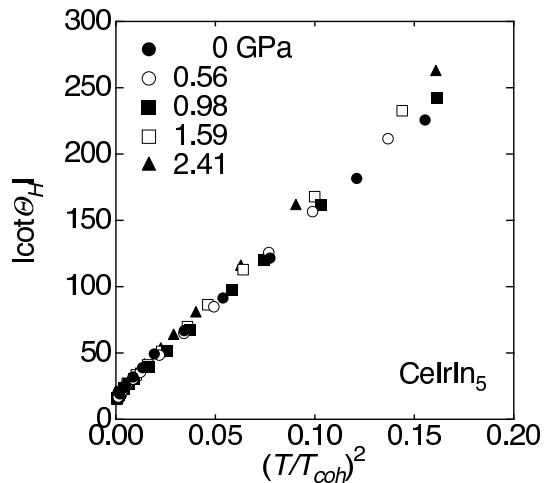


FIG. 5: $|\cot \Theta_H|$ as a function of $(T/T_{coh})^2$ for CeIrIn₅ at 0 (●), 0.56 (○), 0.98 (■), 1.59 (□), and 2.41 GPa (▲).

magnetic fields.

We here comment on the effect of the skew scattering. Usually, R_H in heavy fermion compounds can be written by the sum of the ordinary Hall part R_H^n due to Lorentz force and the anomalous Hall part R_H^a due to skew scattering,²⁵

$$R_H = R_H^n + R_H^a. \quad (2)$$

The magnitude of R_H^a is often much larger than that of R_H^n except for $T \ll T_{coh}$ and $T \gg T_{coh}$. In most Ce-based heavy fermion systems, R_H^a is positive in sign and shows a strong T -dependence, which is scaled by $\chi\rho_{xx}$ (Ref. 25) or χ .²⁶ At around T_{coh} , R_H^a shows a broad maximum and its amplitude becomes much larger than $1/|ne|$. It is obvious that R_H of CeIrIn₅ and CeRh_{0.2}Ir_{0.8}In₅ are very different from that expected from the skew scattering. In fact, the sign of R_H is negative in the whole temperature regime. Moreover, R_H is close to $1/ne$ at $T \sim T_{coh}$. A slight increase of R_H observed at $T \gtrsim T_{coh}$ in the low pressure regime appears to come from small but finite contribution of the skew scattering. Thus the skew scattering contribution is small in CeIrIn₅ and CeRh_{0.2}Ir_{0.8}In₅ and the normal part of Hall effect is dominant. We also note that skew scattering is negligibly small in CeRhIn₅ and CeCoIn₅.^{21,22,23}

The Hall effect in CeIrIn₅ and CeRh_{0.2}Ir_{0.8}In₅ below T_{coh} , particularly the enhancement of $|R_H|$ from $|1/ne|$, is distinctly different from that expected in the conventional metals. Such an enhancement has also been reported in CeCoIn₅ and CeRhIn₅, and high- T_c cuprates. There, it has been shown that the Hall problem can be simplified when analyzed in terms of Hall angle $\Theta_H \equiv \tan^{-1} \frac{\rho_{xy}}{\rho_{xx}}$; $\cot \Theta_H$ well obeys a T^2 -dependence,

$$\cot \Theta_H = AT^2 + B, \quad (3)$$

where A and B are constants.^{27,28,29} We here examine $\cot \Theta_H$ for CeIrIn₅. Figure 5 depicts $\cot \Theta_H$ as a function

of T^2 for CeIrIn₅. In the all pressure regime, $\cot \Theta_H$ well obeys a T^2 -dependence, except for the low temperature regime, exhibiting a striking similarity with CeCoIn₅ and CeRhIn₅, and high- T_c cuprates.

C. Magnetoresistance

Figures 6 (a) and (b) show the magnetoresistance $\Delta\rho_{xx}/\rho_{xx}(0) \equiv (\rho_{xx}(H) - \rho_{xx}(0))/\rho_{xx}(0)$ of CeIrIn₅ at ambient pressure and at $P = 2.41$ GPa, respectively. The magnetoresistance varies as $\Delta\rho_{xx}/\rho_{xx}(0) \propto H^2$ at very low field ($\mu_0 H < 0.2$ T). At ambient pressure, the magnetoresistance decreases with H at high fields below 5 K. This phenomena has also been observed in CeCoIn₅ at ambient pressure^{21,23} and is attributed to the spin-flop scattering.

We here discuss the magnetoresistance in the conventional and unconventional metals. In conventional metals, the magnetoresistance due to orbital motion of carriers obeys the Kohler's rule,

$$\frac{\Delta\rho_{xx}(H)}{\rho_{xx}(0)} = F\left(\frac{\mu_0 H}{\rho_{xx}(0)}\right), \quad (4)$$

where $F(x)$ is a function which depends on the details of electronic structure.³⁰ It has been shown that the magnetoresistance in LaRhIn₅ with similar electronic structure but with weak electronic correlation well obeys the Kohler's rule.²³ We first test the validity of the Kohler's rule in the magnetoresistance of CeIrIn₅. Figures 7(a)

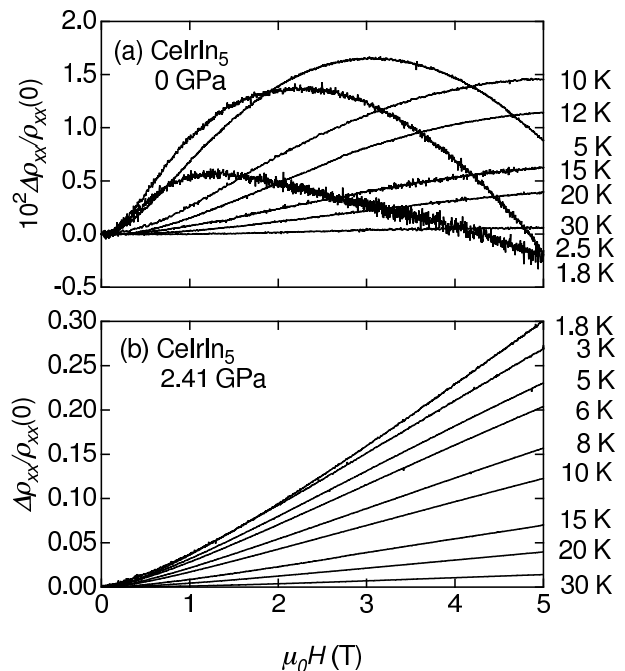


FIG. 6: Magnetoresistance of CeIrIn₅ as a function of H at (a) 0 GPa and (b) 2.41 GPa.

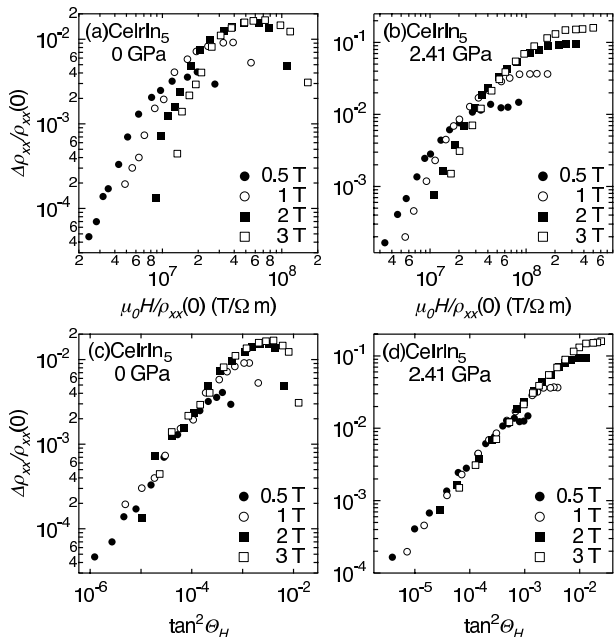


FIG. 7: Kohler's plot. $\Delta\rho_{xx}/\rho_{xx}(0)$ vs $\mu_0 H/\rho_{xx}(0)$ for CeIrIn₅ at (a) 0 GPa, and (b) 2.41 GPa. Modified Kohler's plot. $\Delta\rho_{xx}/\rho_{xx}(0)$ as a function of $\tan^2 \Theta_H$ for CeIrIn₅ at (c) 0 GPa and (d) 2.41 GPa.

and (b) depict $\Delta\rho_{xx}/\rho_{xx}(0)$ of CeIrIn₅ as a function of $\mu_0 H/\rho_{xx}(0)$ at 0 and 2.41 GPa, respectively. The data never collapse into the same curve, indicating a violation of the Kohler's rule.

A striking violation of the Kohler's rule has been reported in CeCoIn₅ and CeRhIn₅, and high- T_c cuprates. It has been shown instead that in these systems the magnetoresistance is well scaled by $\tan^2 \Theta_H$ (modified Kohler's rule), where $\Theta_H \equiv \tan^{-1}(\rho_{xy}/\rho_{xx})$ is the Hall angle;^{21,23,31}

$$\frac{\Delta\rho_{xx}}{\rho_{xx}(0)} \propto \tan^2 \Theta_H. \quad (5)$$

We then examine the validity of the modified Kohler's rule for CeIrIn₅. In Figs. 7(c) and (d), the same data of magnetoresistance are plotted as a function of $\tan^2 \Theta_H$. For both cases, the data collapse into the same curve for three orders of magnitude, indicating that the magnetoresistance well obeys modified Kohler's rule. The deviation from the modified Kohler's rule is observed at low temperature and high field region, possibly due to the spin-flop scattering.

IV. DISCUSSION

Summarizing the salient features in the transport properties of CeIrIn₅ below T_{coh} , which corresponds to the Fermi temperature of f electrons,

- (i) The dc-resistivity shows non-quadratic dependence, $\rho_{xx} \propto T^\alpha$ with α close to unity at ambient pressure.
- (ii) $|R_H|$ increases with decreasing temperature and reaches a value much larger than $|1/ne|$ well below T_{coh} . The Hall angle varies as $\cot \Theta_H \propto T^2$.
- (iii) Magnetoresistance displays T - and H - dependence that strongly violates the Kohler's rule, $\Delta\rho_{xx}(H)/\rho_{xx}(0) \neq F(\mu_0 H/\rho_{xx}(0))$. Magnetoresistance well obeys the modified Kohler's rule that indicates a scaling by the the Hall angle, $\Delta\rho_{xx}/\rho_{xx} \propto \tan^2 \Theta_H$.

It should be emphasized that all of these features bear striking resemblance to those observed in CeCoIn₅, CeRhIn₅, and high- T_c cuprates. Therefore, it is natural to consider that the transport properties commonly observed in CeIrIn₅ originate from the same mechanism.

Our previous studies have shown that the anomalous features in the transport phenomena (i)–(iii) can be accounted for in terms of the recent theory in which the anisotropic inelastic scattering due to AF spin fluctuations are taken into account. In the presence of strong AF fluctuations, the transport scattering rate strongly depends on the position of the Fermi surface. Then the hot spots, at which the electron scattering rate is strongly enhanced by the AF fluctuations, appear at the positions where the AF Brillouin zone intersects with the Fermi surface. The presence of the hot spots has been confirmed in high- T_c cuprates and CeIn₃.³² Since the hot spot area does not contribute to the electron transport, it reduces the effective carrier density, which results in the enhancement of the $|R_H|$ from $|1/ne|$. In such a situation, various transport properties are determined by τ_{cold} , where τ_{cold} is the scattering time of the cold spots on the Fermi surface, at which the electrons are less scattered. Moreover, it has been shown that the transport properties are modified by the *backflow* accompanied with the anisotropic inelastic scattering.^{33,34,35,36}

According to Refs. 33,34,35,36, the transport properties under magnetic fields are governed by the AF correlation length ξ_{AF} in the presence of backflow effect. Zero-field diagonal conductivity $\sigma_{xx}(0)$, Hall conductivity σ_{xy} and magnetoconductivity $\Delta\sigma_{xx}(H) \equiv \sigma_{xx}(H) - \sigma_{xx}(0)$ are given as

$$\sigma_{xx}(0) \sim \tau_{cold}, \quad (6)$$

$$\sigma_{xy} \sim \xi_{AF}^2 \tau_{cold}^2 H, \quad (7)$$

and

$$\Delta\sigma_{xx} \sim \xi_{AF}^4 \tau_{cold}^3 H^2. \quad (8)$$

Here, we have dropped the higher terms with respect to $\tau_{cold} H$ since $\Delta\rho/\rho_0 \ll 1$ in the present experiment, which suggests that the relation $\omega_c \tau \ll 1$ is satisfied. In the

presence of AF fluctuation, ξ_{AF} depends on T as $\xi_{AF}^2 \propto 1/(T + \theta)$, where θ is the Weiss temperature. Moreover, according to AF spin fluctuation theory, τ_{cold} is nearly inversely proportional to T ; $\tau_{cold} \propto 1/T$.³³ When $T \gg \theta$, we then obtain the temperature dependence of the resistivity, $\rho_{xx} = \sigma_{xx}^{-1}$, Hall coefficient, $R_H = \sigma_{xy}/\sigma_{xx}^2 H$, and the Hall angle as

$$\rho_{xx} \propto \tau_{cold}^{-1} \propto T, \quad (9)$$

$$R_H \propto \xi_{AF}^2 \propto \frac{1}{T}, \quad (10)$$

and

$$\cot \Theta_H \propto T^2. \quad (11)$$

By definition, the magnetoresistance is given by

$$\frac{\Delta \rho_{xx}(H)}{\rho_{xx}(0)} = -\frac{\Delta \sigma_{xx}(H)}{\sigma_{xx}(0)} - \left(\frac{\sigma_{xy}(H)}{\sigma_{xx}(0)} \right)^2. \quad (12)$$

Using the relation $\Delta \sigma_{xx}(H)/\sigma_{xy}(H)^2 \sim \tau_{cold}^{-1}$, given by Eqs. (7) and (8), the magnetoresistance is obtained as

$$\frac{\Delta \rho_{xx}(H)}{\rho_{xx}(0)} = (\tan \Theta_H)^2 \cdot \left(\frac{\sigma_{xx}(H)}{\sigma_{xx}(0)} \right)^2 \cdot (C - 1), \quad (13)$$

where C is a constant and is ~ 10 - 100 for CeMIn_5 . Since $\sigma_{xx}(H)/\sigma_{xx}(0) \simeq 1$ at low fields, $\Delta \rho_{xx}(H)/\rho_{xx}(0)$ is well scaled by $\tan^2 \Theta_H$. Thus Eqs. (9), (10), (11), and (13) reproduce the salient features of resistivity, Hall coefficient, Hall angle, and magnetoresistance observed in CeIrIn_5 , respectively.

The H -dependence of R_H shown in the insets of Fig. 4(a) reinforces the conclusion that the AF fluctuations govern the electron transport phenomena in CeIrIn_5 (also in $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$). The enhancement of $|R_H|$ below T_{coh} is strongly suppressed by magnetic fields and approaches that of R_H of LaIrIn_5 . This is consistent with the recovery of the Fermi liquid state in magnetic fields in CeIrIn_5 . Similar phenomena have also been reported in CeCoIn_5 and CeRhIn_5 , where the Fermi liquid state is recovered in magnetic fields by the suppression of AF fluctuations.²³

The upturn behavior of R_H for CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ at low temperatures below T_m shown in Figs. 4 (a) and (b) is also observed in CeCoIn_5 .^{21,22,23} This phenomenon can be explained by the reduction of *backflow* effect due to the effect of the impurity scattering. Below T_m , isotropic impurity scattering becomes dominant and the *backflow* effect due to anisotropic scattering is relatively reduced.^{22,23} To obtain more insight into the impurity effect, we compare the resistivity values at T_m . The small open circles in the insets of Figs. 2 (a) and (b) indicate the resistivity at T_m where R_H shows a minimum. The values of the resistivity at T_m are nearly pressure independent and close to $\sim 5 \mu\Omega\text{cm}$ and $\sim 8 \mu\Omega\text{cm}$ in CeIrIn_5 and $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$, respectively. We note

that these values are close to the values of ρ_{xx} at T_m for CeCoIn_5 .

We here discuss the difference between CeIrIn_5 and $\text{CeCu}_2(\text{Si}_{1-x}\text{Ge}_x)_2$. For $\text{CeCu}_2(\text{Si}_{1-x}\text{Ge}_x)_2$ in the second superconducting dome, anomalous behavior in transport and thermodynamic properties are observed near the pressure P_v , where T_c shows a maximum. For instance, α in Eq. (1) approaches unity and residual resistivity ρ_0 exhibits a maximum near P_v .¹⁸ For CeIrIn_5 , on the other hand, α approaches the Fermi liquid value at $P \sim 3$ GPa, where T_c shows a maximum. Moreover, the residual resistivity decreases with pressure as shown in the insets of Fig. 2, which could be caused by the backflow or enhancement of impurity scattering near AF QCP.³⁶ These results indicate that there seems to be crucial differences in the transport phenomena between CeIrIn_5 and $\text{CeCu}_2(\text{Si}_{1-x}\text{Ge}_x)_2$.

The presence of the AF fluctuations in CeIrIn_5 has been reported by the measurements of the nuclear magnetic resonance (NMR) relaxation rate T_1^{-1} . According to NMR results, AF fluctuations are strongly suppressed with pressure and there is no indication of the AF fluctuations at $P \gtrsim 1$ GPa.¹⁰ The present results indicate that the transport measurements are more sensitive to the AF fluctuations than NMR experiments.

We finally comment on the superconducting gap structure in CeIrIn_5 . Recent measurements of the anisotropy of the inter- and in-plane thermal conductivity for CeIrIn_5 suggest a hybrid gap structure,³⁷ whose symmetry is different from $d_{x^2-y^2}$ for CeCoIn_5 (Refs. 38,39,40) and (most probably) for CeRhIn_5 . However, very recent thermal conductivity measurements under rotated magnetic fields suggest that the superconducting gap structure for CeIrIn_5 has $d_{x^2-y^2}$ symmetry,⁴¹ which implies that the AF spin fluctuations are important for the occurrence of the superconductivity for CeIrIn_5 , which is consistent with the present work.

V. CONCLUSION

We have investigated the detailed electron transport properties by applying pressure in the normal state of $\text{CeRh}_{0.2}\text{Ir}_{0.8}\text{In}_5$ and CeIrIn_5 , which locates in the first and second superconducting dome, respectively. We observed striking non-Fermi liquid behaviors below T_{coh} , including non-quadratic T -dependence of the resistivity, large enhancement of the Hall coefficient at low temperatures ($|R_H| \gg 1/|ne|$), and the violation of the Kohler's rule in the magnetoresistance $\Delta \rho_{xx}(H)/\rho_{xx} \neq F(\mu_0 H/\rho_{xx})$. Moreover, we showed that the cotangent of Hall angle $\cot \Theta_H$ varies as T^2 , and the magnetoresistance is quite well scaled by the Hall angle as $\Delta \rho_{xx}/\rho_{xx} \propto \tan^2 \Theta_H$. These non-Fermi liquid properties, particularly the Hall effect, are suppressed by pressure and magnetic fields. The observed transport anomalies are common features of CeIrIn_5 , CeCoIn_5 , CeRhIn_5 , and high- T_c cuprates. These results lead us to conclude

that the non-Fermi liquid behavior observed in the transport properties in CeIrIn₅ originates not from the C-
valence fluctuations but from the low-lying excitation due
to the AF fluctuations that still remain in the second
dome away from the first dome in the proximity to the
AF QCP.

Acknowledgment

We thank H. Ikeda, K. Miyake and S. Watanabe for
stimulating discussions. This work was partly supported

by a Grant-in-Aid for Scientific Reserch from the Min-
istry of Education, Culture, Sports, Science and Tech-
nology.

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